

## Inchange Semiconductor

## Product Specification

## Silicon PNP Power Transistors

## 2SB1065

## DESCRIPTION

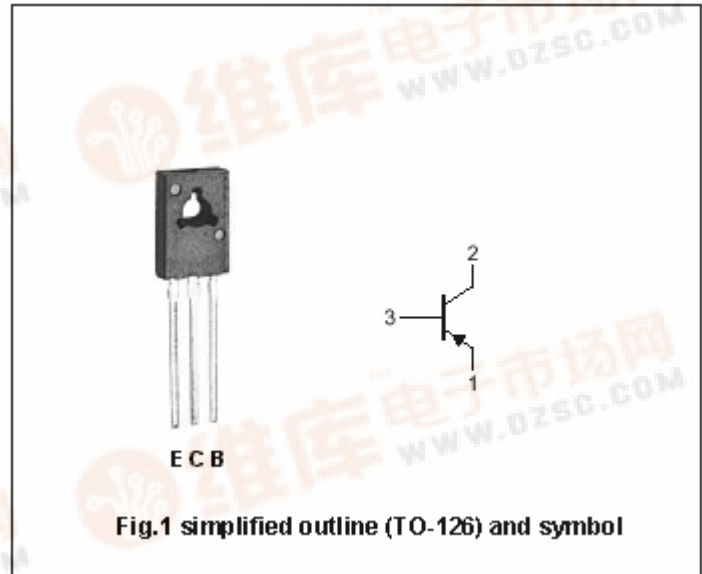
- With TO-126 package
- Complement to type 2SD1506
- Low collector saturation voltage

## APPLICATIONS

- For use in low frequency power amplifier applications

## PINNING

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Emitter                              |
| 2   | Collector;connected to mounting base |
| 3   | Base                                 |

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                 | CONDITIONS     | VALUE   | UNIT |
|-----------|---------------------------|----------------|---------|------|
| $V_{CBO}$ | Collector-base voltage    | Open emitter   | -60     | V    |
| $V_{CEO}$ | Collector-emitter voltage | Open base      | -50     | V    |
| $V_{EBO}$ | Emitter-base voltage      | Open collector | -5      | V    |
| $I_C$     | Collector current         |                | -3      | A    |
| $I_{CM}$  | Collector current-peak    |                | -4.5    | A    |
| $P_D$     | Total power dissipation   | $T_C=25$       | 10      | W    |
| $T_j$     | Junction temperature      |                | 150     |      |
| $T_{stg}$ | Storage temperature       |                | -55~150 |      |

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## CHARACTERISTICS

Tj=25 unless otherwise specified

| SYMBOL        | PARAMETER                            | CONDITIONS                   | MIN | TYP. | MAX  | UNIT    |
|---------------|--------------------------------------|------------------------------|-----|------|------|---------|
| $V_{(BR)CEO}$ | Collector-emitter breakdown voltage  | $I_C=-1mA, I_B=0$            | -50 |      |      | V       |
| $V_{(BR)CBO}$ | Collector-base breakdown voltage     | $I_C=-50\mu A, I_E=0$        | -60 |      |      | V       |
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage       | $I_E=-50\mu A, I_C=0$        | -5  |      |      | V       |
| $V_{CEsat}$   | Collector-emitter saturation voltage | $I_C=-2A; I_B=-0.2A$         |     |      | -1.0 | V       |
| $V_{BEsat}$   | Base-emitter saturation voltage      | $I_C=-2A; I_B=-0.2A$         |     |      | -1.5 | V       |
| $I_{CBO}$     | Collector cut-off current            | $V_{CB}=-40V; I_E=0$         |     |      | -1.0 | $\mu A$ |
| $I_{EBO}$     | Emitter cut-off current              | $V_{EB}=-4V; I_C=0$          |     |      | -1.0 | $\mu A$ |
| $h_{FE}$      | DC current gain                      | $I_C=-0.5A; V_{CE}=-3V$      | 56  |      | 390  |         |
| $C_{OB}$      | Output capacitance                   | $I_E=0; V_{CB}=-10V, f=1MHz$ |     | 50   |      | pF      |
| $f_T$         | Transition frequency                 | $I_C=-0.5A; V_{CE}=-5V$      |     | 70   |      | MHz     |

◆  $h_{FE}$  Classifications

| N      | P      | Q       | R       |
|--------|--------|---------|---------|
| 56-120 | 82-180 | 120-270 | 180-390 |

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PACKAGE OUTLINE

